Icemos Technology Ltd Product Specification 1000.519702 Issue Date 16 January 2018 15:2'

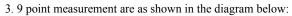
Part Number	Customer	

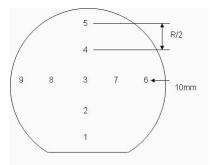
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	647.00 +/- 6.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	3mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	525.00 +/- 5.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 – 50 Ohmem	Wafer Vendor
	17.0	Backside Finish	Polished with lasermark and oxide.	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	120.00 +/- 1.00 μm	ADE Single point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by process
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	Red Phosphorous	Wafer Vendor
	27.0	Device Resistivity	0.0001 – 0.0015 Ocm	Wafer Vendor
	28.0	Oxygen Concentration	<15.00ppma	Wafer Supplier
	29.0	Voids	All wafers scanned for voids by Scanning Acoustic Microscope (SAM)	SAM & Bright Light, 100% (note 2)
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

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Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	tion performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall			

Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information